

BUK7Y13-40B

N-channel TrenchMOS standard level FET

Rev. 02 — 2 October 2007

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode power Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology.

1.2 Features

- Very low on-state resistance
- 175 °C rated
- Q101 compliant
- Standard level compatible

1.3 Applications

- Automotive ABS systems
- Motors, lamps and solenoids
- Diesel injection systems
- Automotive transmission control
- Fuel pump and injection
- Airbag

1.4 Quick reference data

- $E_{DS(AL)S} \leq 91$ mJ
- $I_D \leq 55$ A
- $R_{DSon} = 11$ m Ω (typ)
- $P_{tot} \leq 75$ W

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1, 2, 3	source (S)	<p style="text-align: center;">SOT669 (LPAK)</p>	<p style="text-align: center;">mb1798</p>
4	gate (G)		
mb	mounting base; connected to drain (D)		

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BUK7Y13-40B	LFPAK	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Limiting values

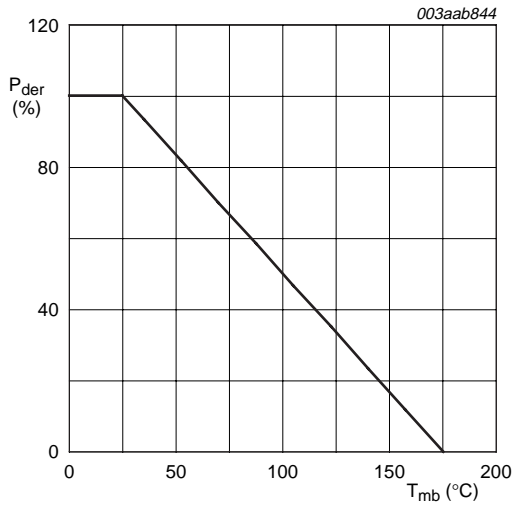
Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	40	V
V_{DGR}	drain-gate voltage (DC)	$R_{GS} = 20 \text{ k}\Omega$	-	40	V
V_{GS}	gate-source voltage		-	± 20	V
I_D	drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; $V_{GS} = 10 \text{ V}$; see Figure 2 and 3	-	55	A
		$T_{mb} = 100 \text{ }^\circ\text{C}$; $V_{GS} = 10 \text{ V}$; see Figure 2	-	38	A
I_{DM}	peak drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$; see Figure 3	-	220	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; see Figure 1	-	75	W
T_{stg}	storage temperature		-55	+175	$^\circ\text{C}$
T_j	junction temperature		-55	+175	$^\circ\text{C}$
Source-drain diode					
I_{DR}	reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	55	A
I_{DRM}	peak reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$	-	220	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	Unclamped inductive load; $I_D = 55 \text{ A}$; $V_{DS} \leq 40 \text{ V}$; $V_{GS} = 10 \text{ V}$; $R_{GS} = 50 \text{ }\Omega$; starting at $T_j = 25 \text{ }^\circ\text{C}$	-	91	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		-	[1]	-

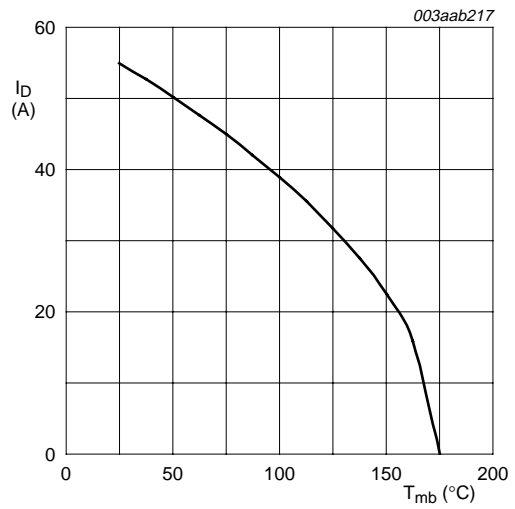
[1] Conditions:

- a) Maximum value not quoted. Repetitive rating defined in [Figure 16](#).
- b) Single-pulse avalanche rating limited by $T_{j(max)}$ of 175 $^\circ\text{C}$.
- c) Repetitive avalanche rating limited by an average junction temperature of 170 $^\circ\text{C}$.
- d) Refer to application note *AN10273* for further information.



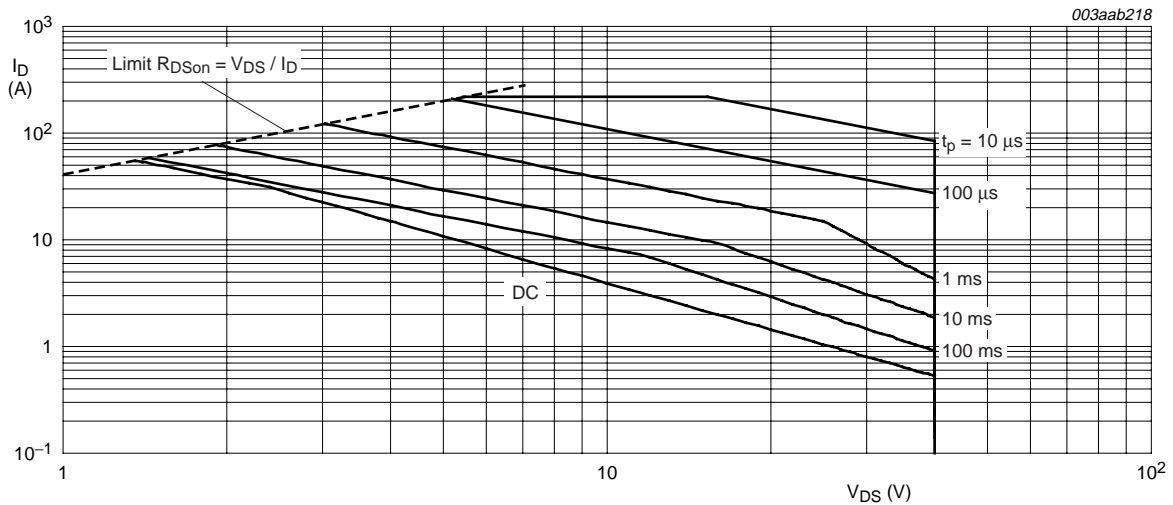
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature



V_{GS} ≥ 10 V

Fig 2. Continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	-	-	-	2	K/W

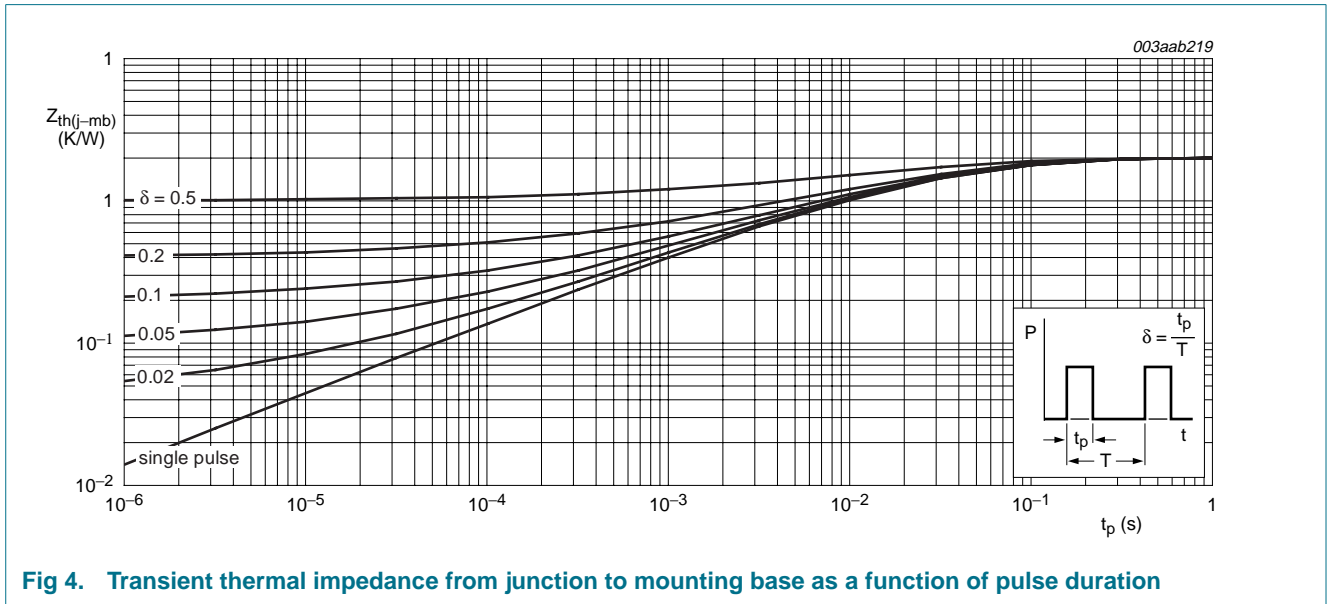


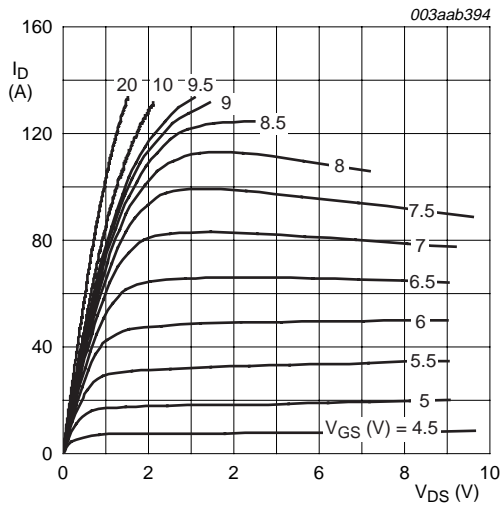
Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5: Characteristics

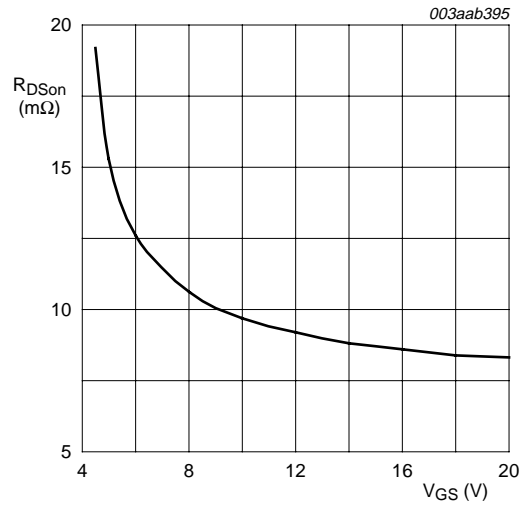
$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	40	-	-	V
		$T_j = -55\text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{DS} = V_{GS}$; see Figure 9 and 10				
		$T_j = 25\text{ °C}$	2	3	4	V
		$T_j = 175\text{ °C}$	1	-	-	V
		$T_j = -55\text{ °C}$	-	-	4.4	V
I_{DSS}	drain leakage current	$V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	-	0.02	1	μA
		$T_j = 175\text{ °C}$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}$; see Figure 6 and 8				
		$T_j = 25\text{ °C}$	-	11	13	m Ω
		$T_j = 175\text{ °C}$	-	-	25	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V}$; see Figure 14	-	19	-	nC
Q_{GS}	gate-source charge		-	6	-	nC
Q_{GD}	gate-drain charge		-	5.1	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$; see Figure 12	-	983	1311	pF
C_{oss}	output capacitance		-	280	336	pF
C_{rss}	reverse transfer capacitance		-	138	189	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 2.5\ \Omega$;	-	9	-	ns
t_r	rise time	$V_{GS} = 10\text{ V}; R_G = 10\ \Omega$	-	25	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
t_f	fall time		-	27	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}$; see Figure 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}$;	-	41	-	ns
Q_r	recovered charge	$V_{GS} = 0\text{ V}; V_R = 30\text{ V}$	-	22	-	nC



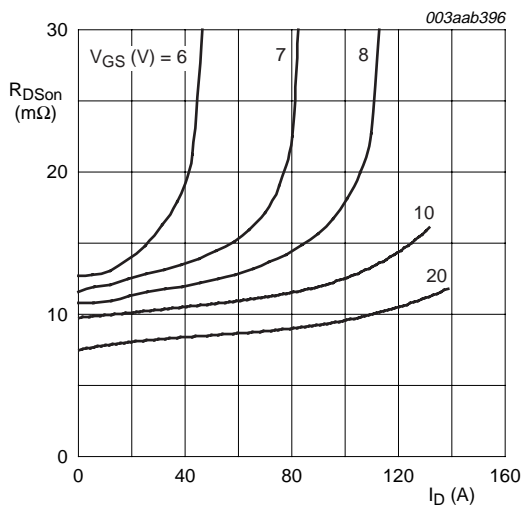
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



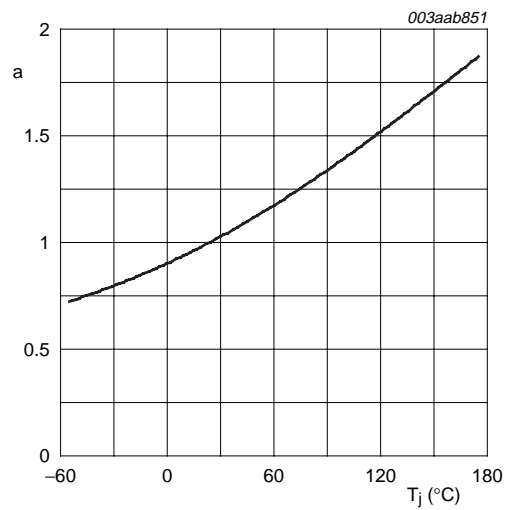
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



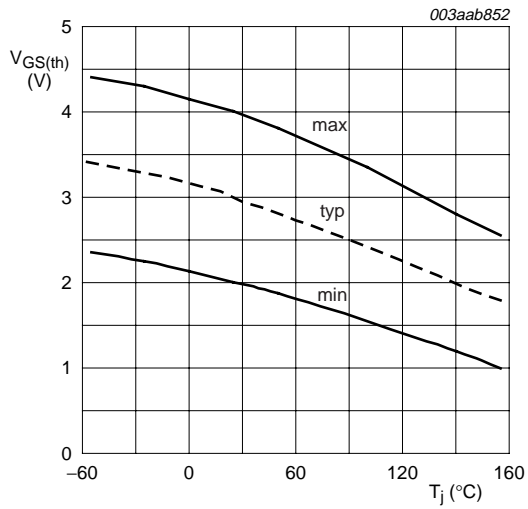
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



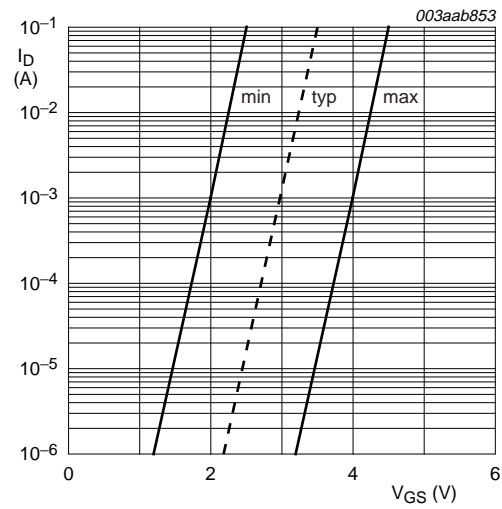
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



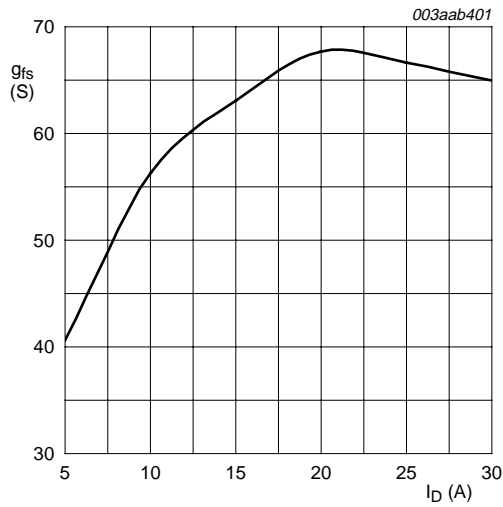
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



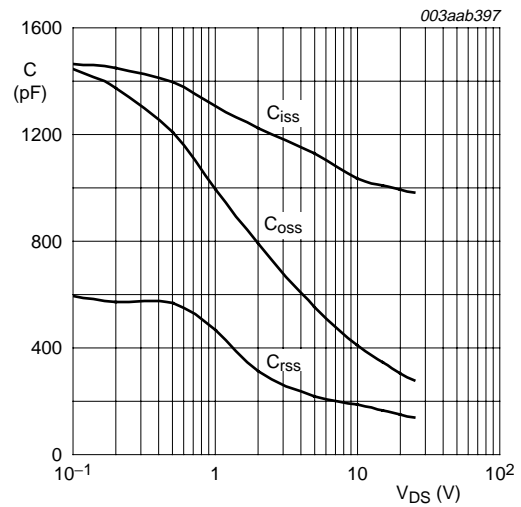
$T_j = 25 \text{ }^{\circ}C; V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25 \text{ }^{\circ}C; V_{DS} = 25 \text{ V}$

Fig 11. Forward transconductance as a function of drain current; typical values



$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

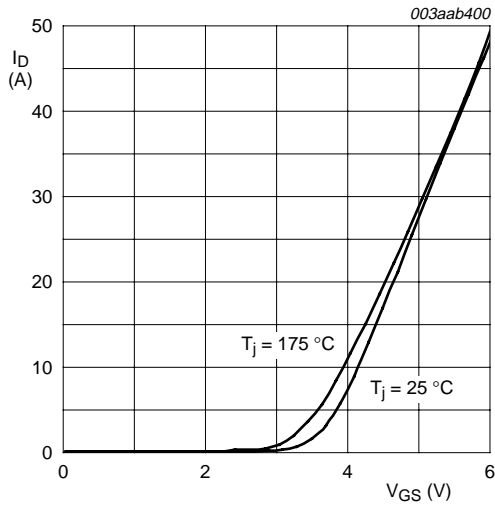


Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values

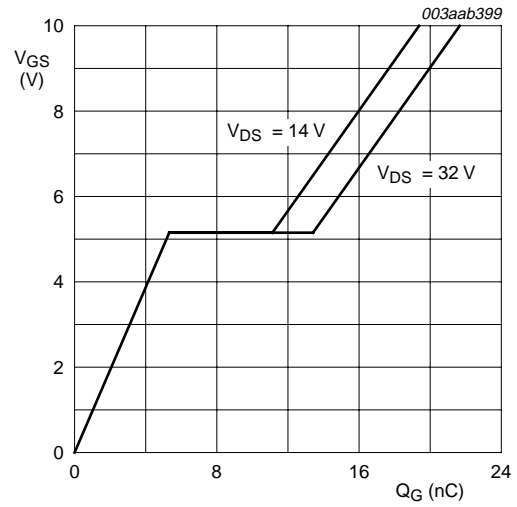


Fig 14. Gate-source voltage as a function of gate charge; typical values

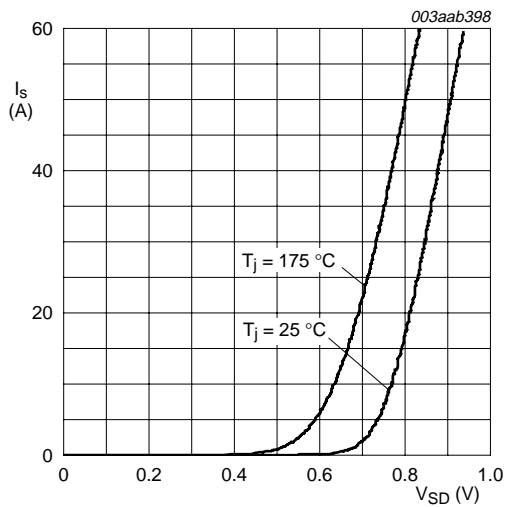
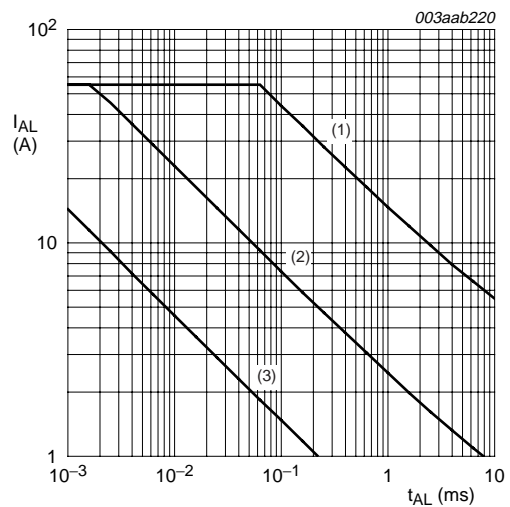


Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



See [Table note 1](#) of [Table 3](#) Limiting values.

- (1) Single-pulse; $T_j = 25\text{ }^\circ\text{C}$.
- (2) Single-pulse; $T_j = 150\text{ }^\circ\text{C}$.
- (3) Repetitive.

Fig 16. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

7. Package outline

Plastic single-ended surface-mounted package (LFAK); 4 leads

SOT669

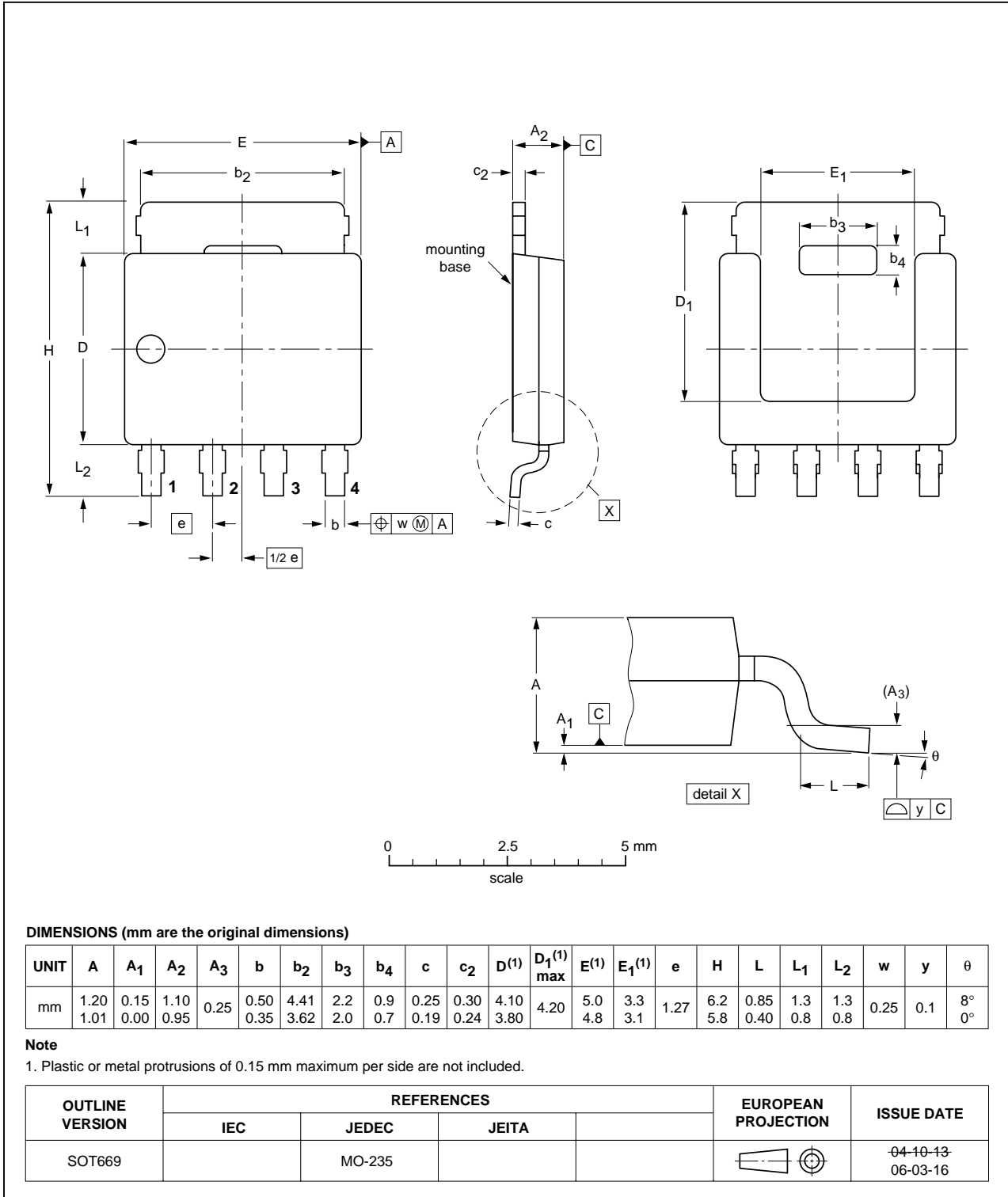


Fig 17. Package outline SOT669 (LFAK)

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y13-40B_2	20071002		-	BUK7Y13-40B_1
Modifications:	<ul style="list-style-type: none">• Changed Descriptive title and Alternative descriptive title variables from "N-channel TrenchMOS logic level FET" to "N-channel TrenchMOS standard level FET".			
BUK7Y13-40B_1	20070924	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	1
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	4
6	Characteristics	5
7	Package outline	9
8	Revision history	10
9	Legal information	11
9.1	Data sheet status	11
9.2	Definitions	11
9.3	Disclaimers	11
9.4	Trademarks	11
10	Contact information	11
11	Contents	12

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Date of release: 2 October 2007

Document identifier: BUK7Y13-40B_2